

Long Zheng

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2759663/publications.pdf>

Version: 2024-02-01

16
papers

186
citations

933447

10
h-index

1058476

14
g-index

16
all docs

16
docs citations

16
times ranked

168
citing authors

#	ARTICLE	IF	CITATIONS
1	Improvement of the thermal stability of Sb thin film through erbium doping. CrystEngComm, 2016, 18, 6365-6369.	2.6	26
2	The microstructural changes of Ge ₂ Sb ₂ Te ₅ thin film during crystallization process. AIP Advances, 2018, 8, .	1.3	21
3	Designing Multiple Crystallization in Superlattice-like Phase-Change Materials for Multilevel Phase-Change Memory. ACS Applied Materials & Interfaces, 2019, 11, 45885-45891.	8.0	20
4	Simultaneous thermal stability and phase change speed improvement of Sn ₁₅ Sb ₈₅ thin film through erbium doping. Journal of Applied Physics, 2016, 120, .	2.5	18
5	Improvement in reliability and power consumption based on Ge ₁₀ Sb ₉₀ films through erbium doping. Journal of Materials Science, 2017, 52, 5216-5222.	3.7	16
6	Interface effect and stress effect on Ge ₂ Sb ₂ Te ₅ /Sb superlattice-like thin films. EPJ Applied Physics, 2017, 77, 30102.	0.7	15
7	High speed and low power consumption of superlattice-like Ge/Sb ₇₀ Se ₃₀ thin films for phase change memory application. Journal of Materials Science: Materials in Electronics, 2016, 27, 2183-2188.	2.2	14
8	Designing artificial carbon clusters using Ge ₂ Sb ₂ Te ₅ /C superlattice-like structure for phase change applications. Journal of Alloys and Compounds, 2021, 882, 160695.	5.5	13
9	O-Doped Sb ₇₀ Se ₃₀ Phase-Change Materials for High Thermal Stability and Fast Speed. Journal of Electronic Materials, 2017, 46, 6811-6816.	2.2	12
10	N-doped Zn ₁₅ Sb ₈₅ phase-change materials for higher thermal stability and lower power consumption. Journal of Materials Science: Materials in Electronics, 2014, 25, 2943-2947.	2.2	11
11	Superlattice-like Ga ₄₀ Sb ₆₀ /Sb films with ultra-high speed and low power for phase change memory application. Journal of Materials Science: Materials in Electronics, 2017, 28, 3806-3811.	2.2	9
12	Layer thickness dependence of the phase separation and phase change properties of Ge ₂ Sb ₂ Te ₅ /TiN superlattice-like thin films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2018, 238-239, 71-75.	3.5	4
13	Chromium doped GeTe for low-power-consumption phase change memory. EPJ Applied Physics, 2020, 92, 30101.	0.7	3
14	The improvement of phase-change properties on Ge ₂ Sb ₂ Te ₅ using the superlattice-like structure. EPJ Applied Physics, 2017, 80, 30101.	0.7	2
15	Impact of atomic vacancy on phase change and structure in Ge _x Te _{1-x} films. Journal of Materials Science: Materials in Electronics, 2020, 31, 5936-5940.	2.2	2
16	Structure study on SrRu _{1-x} MnxO ₄ using the extended X-ray absorption fine structure spectroscopy. Journal of X-Ray Science and Technology, 2015, 23, 611-616.	1.0	0